

PMEM4020APD

PNP transistor/Schottky rectifier module

Rev. 01 — 4 October 2004

Product data sheet

1. Product profile

1.1 General description

Combination of a PNP transistor with low V_{CEsat} and high current capability and a planar Schottky barrier rectifier with an integrated guard ring for stress protection in a SOT457 (SC-74) small plastic package. NPN complement: PMEM4020AND.

1.2 Features

- 600 mW total power dissipation
- High current capability up to 2 A
- Reduces printed-circuit board area required
- Reduces pick and place costs
- Small plastic SMD package
- Transistor
 - ◆ Low collector-emitter saturation voltage.
- Diode
 - ◆ Ultra high-speed switching
 - ◆ Very low forward voltage
 - ◆ Guard ring protected.

1.3 Applications

- DC-to-DC converters
- Inductive load drivers
- General purpose load drivers
- Reverse polarity protection circuits
- MOSFET drivers.

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PNP transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
I_C	collector current (DC)	continuous; $T_s \leq 55\text{ °C}$	[1] -	-	-2	A

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Table 1: Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Schottky barrier rectifier						
V_R	continuous reverse voltage		-	-	40	V
I_F	continuous forward current		-	-	1	A

[1] Soldering point of collector or cathode tab.

2. Pinning information

Table 2: Discrete pinning

Pin	Description	Simplified outline	Symbol
1	emitter	<p style="text-align: center;">SOT457</p>	<p style="text-align: center;">sym040</p>
2	not connected		
3	cathode		
4	anode		
5	base		
6	collector		

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PMEM4020APD	SC-74	plastic surface mounted package; 6 leads	SOT457

4. Marking

Table 4: Marking

Type number	Marking code
PMEM4020APD	D3

5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
PNP transistor					
V_{CBO}	collector-base voltage	open emitter	-	-40	V
V_{CEO}	collector-emitter voltage	open base	-	-40	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V

Table 5: Limiting values ...continued
 In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
I _C	collector current (DC)	continuous	[1] -	-0.75	A
		continuous	[2] -	-1	A
		continuous	[3] -	-1.3	A
		continuous; T _s ≤ 55 °C	[4] -	-2	A
I _{CM}	peak collector current		-	-3	A
I _{BM}	peak base current		-	-1	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	295	mW
		T _{amb} ≤ 25 °C	[2] -	400	mW
		T _{amb} ≤ 25 °C	[3] -	500	mW
		T _s ≤ 55 °C	[4] -	1000	mW
T _j	junction temperature		-	150	°C
Schottky barrier rectifier					
V _R	continuous reverse voltage		-	40	V
I _F	continuous forward voltage		-	1	A
I _{FRM}	repetitive peak forward current	t _p ≤ 1 ms; δ ≤ 0.5	-	3.5	A
I _{FSM}	non-repetitive peak forward current	t = 8 ms; square wave	-	10	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	295	mW
		T _{amb} ≤ 25 °C	[2] -	400	mW
		T _{amb} ≤ 25 °C	[3] -	500	mW
		T _s ≤ 55 °C	[4] -	1000	mW
T _j	junction temperature		[2] -	150	°C
Combined device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2] -	600	mW
T _{stg}	storage temperature		-65	+150	°C
T _{amb}	ambient temperature		[2] -65	+150	°C

- [1] Mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint.
- [2] Device mounted on a printed-circuit board, single-sided copper, tin-plated, 1 cm² mounting pad for both collector and cathode.
- [3] Mounted on a ceramic printed-circuit board, single-sided copper, tin-plated, standard footprint.
- [4] Soldering point of collector or cathode tab.

6. Thermal characteristics

Table 6: Thermal characteristics [1]

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Single device						
$R_{th(j-s)}$	thermal resistance from junction to soldering point	in free air	[2] -	-	95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[3] -	-	250	K/W
			[4] -	-	315	K/W
			[5] -	-	425	K/W
Combined device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[3] -	-	208	K/W

[1] For Schottky barrier rectifiers thermal run-away has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

[2] Soldering point of collector or cathode tab.

[3] Mounted on a ceramic printed-circuit board, single-sided copper, tin-plated, standard footprint.

[4] Device mounted on a printed-circuit board, single-sided copper, tin-plated, 1 cm² mounting pad for both collector and cathode tab.

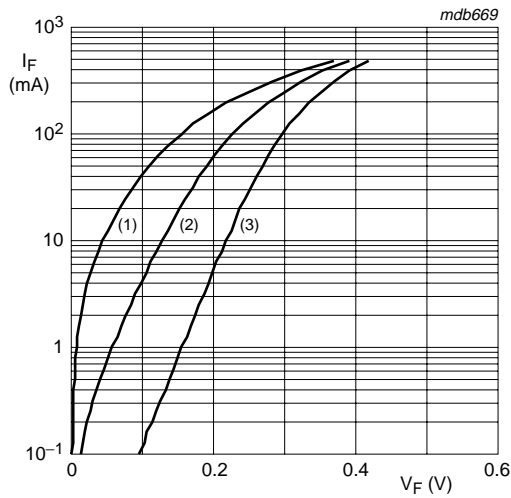
[5] Mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint.

7. Characteristics

Table 7: Characteristics
T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PNP transistor						
I _{CBO}	collector-base cut-off current	V _{CB} = -40 V; I _E = 0 A	-	-	-100	nA
		V _{CB} = -40 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CEO}	collector-emitter cut-off current	V _{CE} = -30 V; I _B = 0 A	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -1 mA	300	-	-	
		V _{CE} = -5 V; I _C = -100 mA	300	-	-	
		V _{CE} = -5 V; I _C = -500 mA	250	-	900	
		V _{CE} = -5 V; I _C = -1 A	160	-	-	
		V _{CE} = -5 V; I _C = -2 A	[1] 50	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -100 mA; I _B = -1 mA	-	-	-120	mV
		I _C = -500 mA; I _B = -50 mA	-	-	-145	mV
		I _C = -1 A; I _B = -100 mA	-	-	-260	mV
		I _C = -2 A; I _B = -200 mA	-	-	-530	mV
R _{CEsat}	equivalent on-resistance	I _C = -1 A; I _B = -100 mA	[1] -	180	280	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = -1 A; I _B = -100 mA	[1] -	-	-1.1	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = -5 V; I _C = -1 A	[1] -	-	-1.0	V
f _T	transition frequency	V _{CE} = -10 V; I _C = -50 mA; f = 100 MHz	150	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = I _e = 0 A; f = 1 MHz	-	-	10	pF
Schottky barrier rectifier						
V _F	continuous forward voltage	see Figure 1				
		I _F = 0.1 mA	[1] -	95	130	mV
		I _F = 1 mA	[1] -	155	210	mV
		I _F = 10 mA	[1] -	220	270	mV
		I _F = 100 mA	[1] -	295	350	mV
		I _F = 1000 mA	[1] -	540	640	mV
I _R	reverse current	see Figure 2				
		V _R = 10 V	[1] -	7	20	μA
		V _R = 40 V	[1] -	30	100	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; see Figure 3	-	43	48	pF

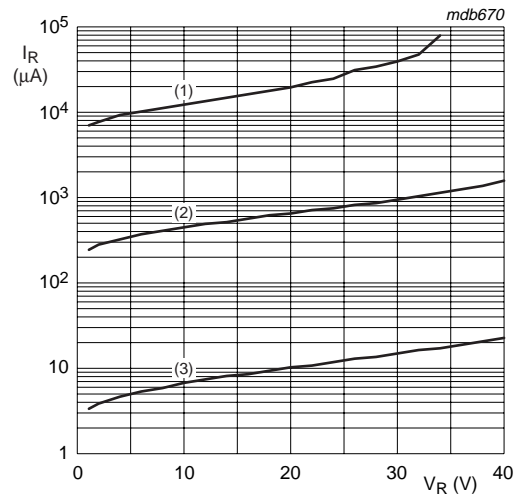
[1] Pulse test: t_p ≤ 300 μs; δ ≤ 0.02.



Schottky barrier rectifier.

- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

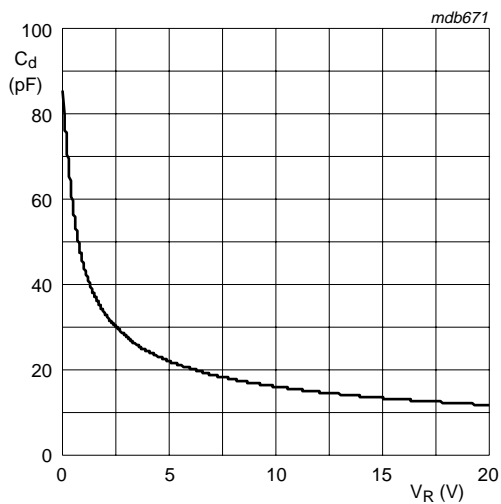
Fig 1. Forward current as a function of forward voltage; typical values.



Schottky barrier rectifier.

- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

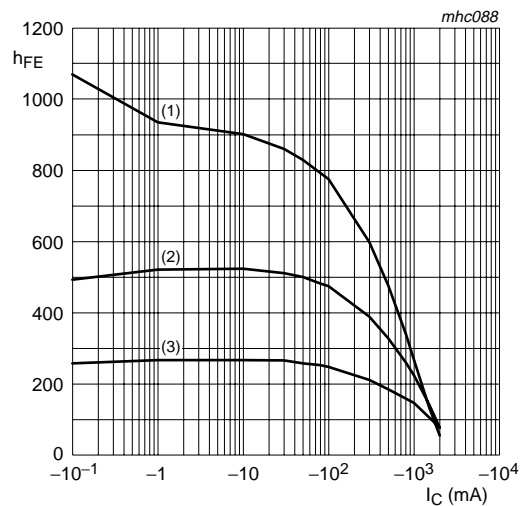
Fig 2. Reverse current as a function of reverse voltage; typical values.



Schottky barrier rectifier;

$T_{amb} = 25\text{ }^{\circ}\text{C}$; $f = 1\text{ MHz}$.

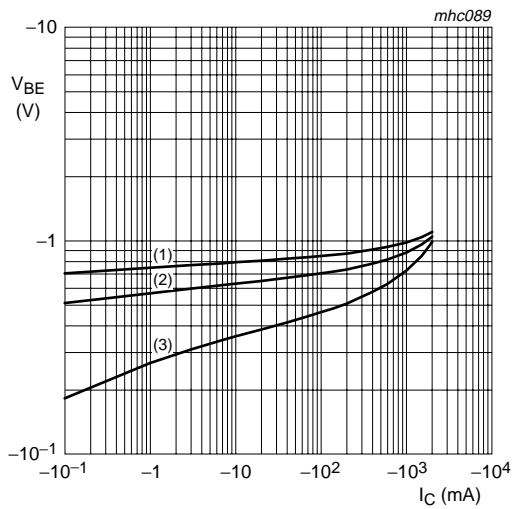
Fig 3. Diode capacitance as a function of reverse voltage; typical values.



PNP transistor; $V_{CE} = -5\text{ V}$.

- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$.

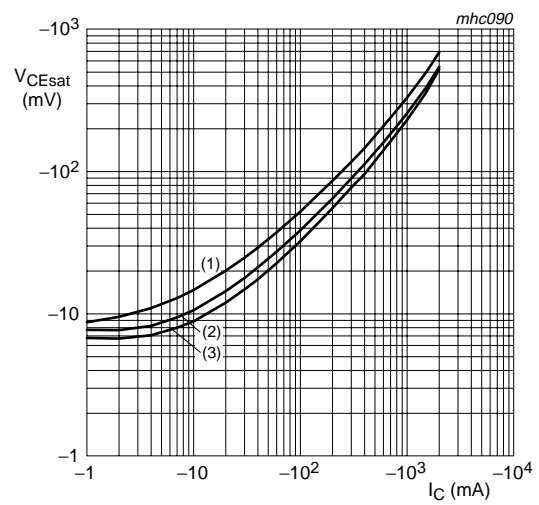
Fig 4. DC current gain as a function of collector current; typical values.



PNP transistor; $V_{CE} = -5$ V.

- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = 150$ °C.

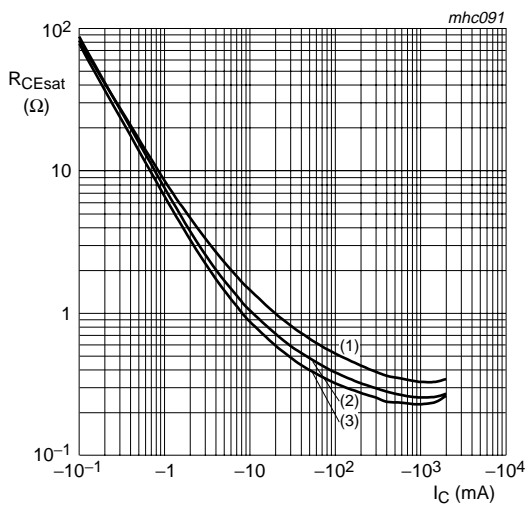
Fig 5. Base-emitter voltage as a function of collector current; typical values.



PNP transistor; $I_C/I_B = 10$.

- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

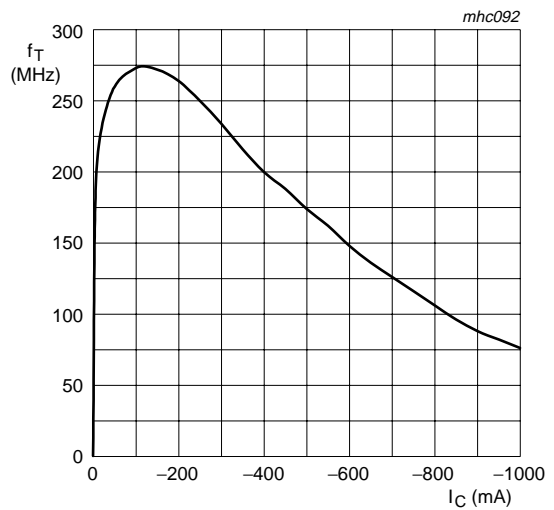
Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values.



PNP transistor; $I_C/I_B = 10$.

- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

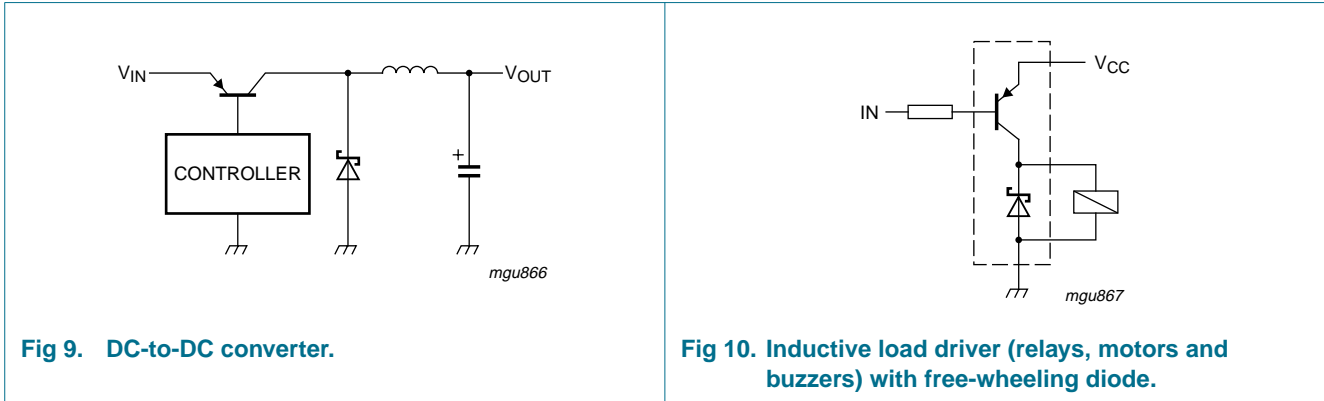
Fig 7. Equivalent on-resistance as a function of collector current; typical values.



PNP transistor; $V_{CE} = -10$ V.

Fig 8. Transition frequency as a function of collector current.

8. Application information



9. Package outline

Plastic surface mounted package; 6 leads

SOT457

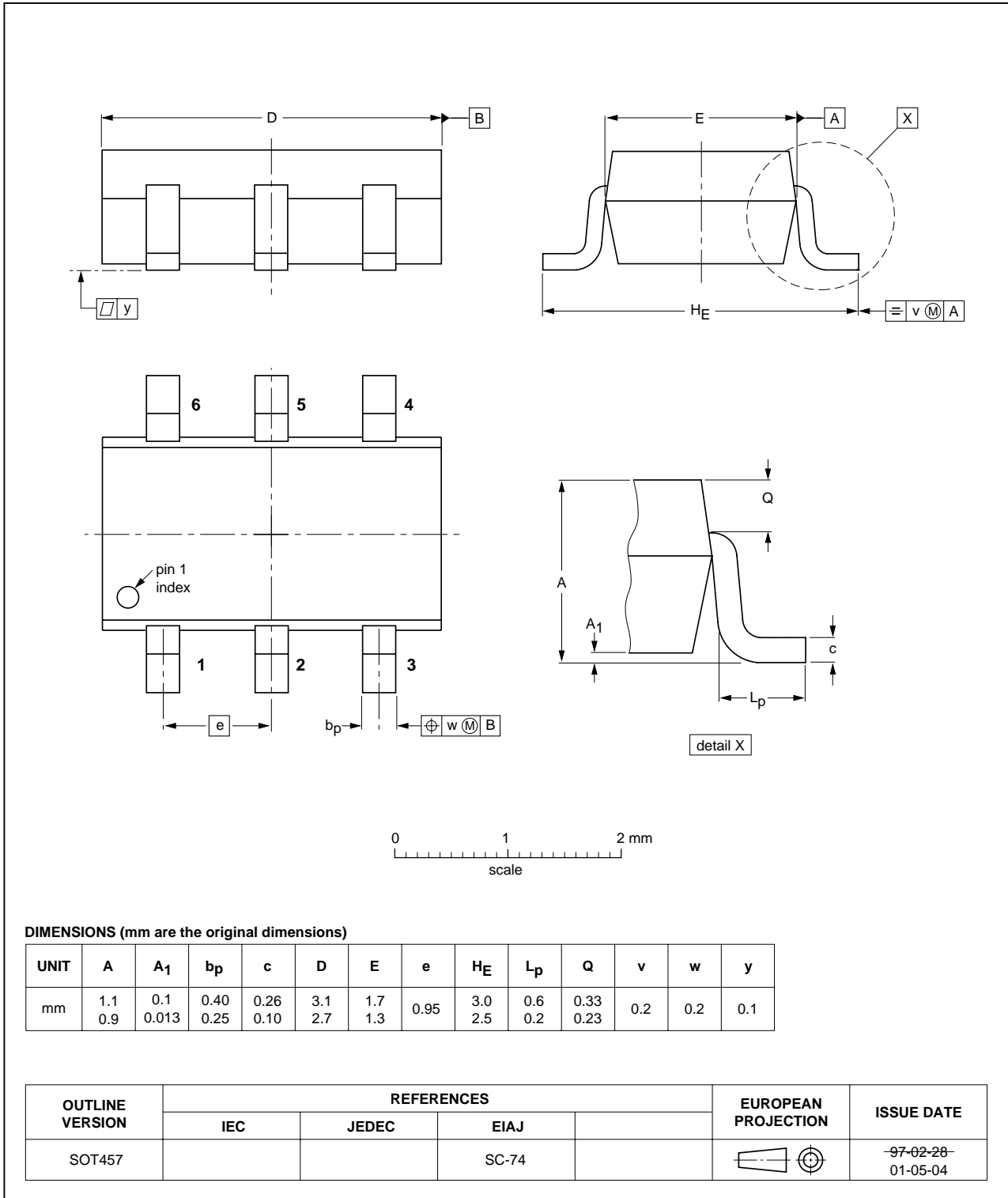


Fig 11. Package outline SOT457 (SC-74).

10. Packing information

Table 8: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [\[1\]](#)

Type number	Package	Description	Packing quantity	
			3000	10000
PMEM4020APD	SOT457	4 mm pitch, 8 mm tape and reel; T1	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-165

[1] For further information and the availability of packing methods, see [Section 15.S](#)



11. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
PMEM4020APD_1	20041004	Product data sheet	-	9397 750 13707	-

12. Data sheet status

Level	Data sheet status ^[1]	Product status ^[2] ^[3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Date of release: 4 October 2004
Document order number: 9397 750 13707

Published in The Netherlands